ICMOVPE
XXII July 12-17, 2026
ICC JEJU, Jeju Island, Korea

Session Title:	**[TuB1] Lasers**
Session Date:	**July 14 (Tue.), 2026**
Session Time:	**08:30-10:15**
Session Room:	**Room B (Baekrok Hall B-2, 1F)**
Session Chairs	

[TuB1-1] [Invited] 08:30-09:00

High Efficiency GaN-Based VCSELs with AlInN/GaN DBRs Grown by MOVPE

Tetsuya Takeuchi, Satoshi Kamiyama, and Motoaki Iwaya, Meijo University, Japan

[TuB1-2] 09:00-09:15

3.2-W InGaN-Based Photonic Crystal Surface Emitting Laser

Qian Sun, Chinese Academy of Sciences, China

[TuB1-3] 09:15-09:30

Void-Retaining Epitaxy for Photonic Crystal Surface Emitting Lasers

A. F. McKenzie[1], S. Kumar[1], N. D. Gerrard[1], D. A. MacLaren[1], S. J. Sweeney[1], and R. A. Hogg[2], [1] University of Glasgow, UK, [2] Aston University, United Kingdom

[TuB1-4] 09:30-09:45

Extending the Concept of Quantum Mechanics to Bottom-Up Semiconductor Lasers

Wei Wen Wong, Xiaoying Huang, Jihua Zhang, Gaurang Garg, Olivier Lee Cheong Lem, Chennupati Jagadish, and Hoe Tan, The Australian National University, Australia

[TuB1-5] 09:45-10:00

A Novel Monolithic High-Contrast Grating VCSEL Grown by MOVPE for Near-Infrared Emission

Mikołaj Badura[1], Justyna Olejnik[1], Wojciech Dawidowski[1], Jan M. Śmigiel[1], Damian Radziewicz[1], Adriana Łozińska[1], Marcin Gębski[2], Magdalena Marciniak[2], Tomasz Czyszanowski[2], Weronika Głowadzka[3], Marek Ekielski[3], Iwona Sankowska[3], Anna Szerling[3], and Beata Ściana[1], [1] Wrocław University of Science and Technology, Poland, [2] Lodz University of Technology, Poland, [3] Łukasiewicz Research Network, Poland

[TuB1-6] 10:00-10:15

Design and Development of InGaN-Based VECSEL Structures for High-Power Single-Mode Green Emission

Lucja Marona, Szymon Grzanka, Agata Bojarska, and Piotr Perlin, Institute of High-Pressure Physics PAS, Poland